

40V N-CHANNEL ENHANCEMENT MODE MOSFET
Product Summary

$V_{(BR)DSS}$	$R_{DS(ON)}$	I_D $T_C = +25^\circ C$
40V	24m Ω @ $V_{GS} = 10V$	28A
	32m Ω @ $V_{GS} = 4.5V$	24A

Description

This MOSFET is designed to minimize the on-state resistance ($R_{DS(ON)}$) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

Applications

- Backlighting
- DC-DC Converters
- Power Management Functions

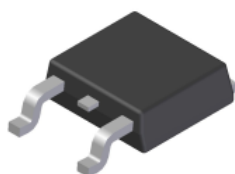
Features

- 100% Unclamped Inductive Switch (UIS) Test in Production
- Low On-resistance
- Fast Switching Speed
- **Totally Lead-Free & Fully RoHS compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**

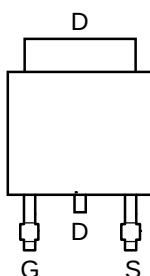
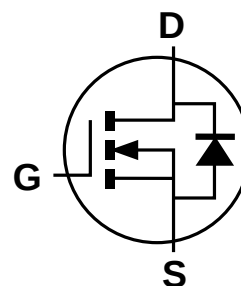
Mechanical Data

- Case: TO252
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Matte Tin Finish Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 
- Weight: 0.33 grams (Approximate)

TO252



Top View

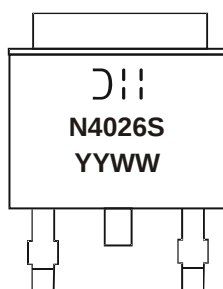

 Top View
Pin-Out


Equivalent Circuit

Ordering Information (Note 4)

Product	Case	Packaging
DMN4026SK3-13	TO252	2,500/Tape & Reel

- Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
 2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
 4. For packaging details, go to our website at <http://www.diodes.com/products/packages.html>.

Marking Information


 = Manufacturer's Marking
 N4026S = Product Type Marking Code
 YYWW = Date Code Marking
 YY = Year (ex: 15 = 2015)
 WW = Week (01 to 53)

Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Unit
Drain-Source Voltage			V _{DSS}	40	V
Gate-Source Voltage			V _{GSS}	±20	V
Continuous Drain Current (Note 6) V _{GS} = 10V	Steady State	T _C = +25°C T _C = +100°C	I _D	28 18	A
Maximum Body Diode Continuous Current			I _S	2.5	A
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)			I _{DM}	70	A
Avalanche Current (Note 7) L = 0.1mH			I _{AS}	18	A
Avalanche Energy (Note 7) L = 0.1mH			E _{AS}	17	mJ

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 5)	T _A = +25°C	P _D	1.6	W
	T _A = +70°C		1.0	
Thermal Resistance, Junction to Ambient (Note 5)	Steady state	R _{θJA}	75	°C/W
	t < 10s		32.7	
Total Power Dissipation (Note 6)	T _A = +25°C	P _D	3.4	W
	T _A = +70°C		2.1	
Thermal Resistance, Junction to Ambient (Note 6)	Steady state	R _{θJA}	37	°C/W
	t < 10s		18.1	
Thermal Resistance, Junction to Case (Note 6)		R _{θJC}	4.5	
Operating and Storage Temperature Range		T _J , T _{STG}	-55 to +150	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 8)						
Drain-Source Breakdown Voltage	BV _{DSS}	40	—	—	V	V _{GS} = 0V, I _D = 250µA
Zero Gate Voltage Drain Current	I _{DSS}	—	—	1	µA	V _{DS} = 40V, V _{GS} = 0V
Gate-Source Leakage	I _{GSS}	—	—	±100	nA	V _{GS} = ±20V, V _{DS} = 0V
ON CHARACTERISTICS (Note 8)						
Gate Threshold Voltage	V _{GS(TH)}	1	—	3	V	V _{DS} = V _{GS} , I _D = 250µA
Static Drain-Source On-Resistance	R _{DS(ON)}	—	15	24	mΩ	V _{GS} = 10V, I _D = 6A
		—	20	32		V _{GS} = 4.5V, I _D = 5A
Diode Forward Voltage	V _{SD}	—	0.7	1.0	V	V _{GS} = 0V, I _S = 1.0A
DYNAMIC CHARACTERISTICS (Note 9)						
Input Capacitance	C _{ISS}	—	1181	—	pF	V _{DS} = 20V, V _{GS} = 0V, f = 1.0MHz
Output Capacitance	C _{OSS}	—	85	—		
Reverse Transfer Capacitance	C _{RSS}	—	63	—		
Gate Resistance	R _G	—	1.5	—	Ω	V _{DS} = 0V, V _{GS} = 0V, f = 1.0MHz
Total Gate Charge (V _{GS} = 4.5V)	Q _g	—	9.6	—	nC	V _{DS} = 20V, I _D = 8A
Total Gate Charge (V _{GS} = 10V)	Q _g	—	21.3	—		
Gate-Source Charge	Q _{GS}	—	3.7	—		
Gate-Drain Charge	Q _{gd}	—	3.0	—		
Turn-On Delay Time	t _{D(ON)}	—	4.3	—	ns	V _{DD} = 25V, R _L = 2.5Ω V _{GS} = 10V, R _G = 3Ω
Turn-On Rise Time	t _R	—	4.6	—		
Turn-Off Delay Time	t _{D(OFF)}	—	19.5	—		
Turn-Off Fall Time	t _F	—	3.1	—		
Body Diode Reverse Recovery Time	t _{RR}	—	12.0	—	ns	I _F = 8A, di/dt = 100A/µs
Body Diode Reverse Recovery Charge	Q _{RR}	—	3.85	—	nC	I _F = 8A, di/dt = 100A/µs

- Notes:
- Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.
 - Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.
 - I_{AS} and E_{AS} ratings are based on low frequency and duty cycles to keep T_J = +25°C.
 - Short duration pulse test used to minimize self-heating effect.
 - Guaranteed by design. Not subject to product testing.

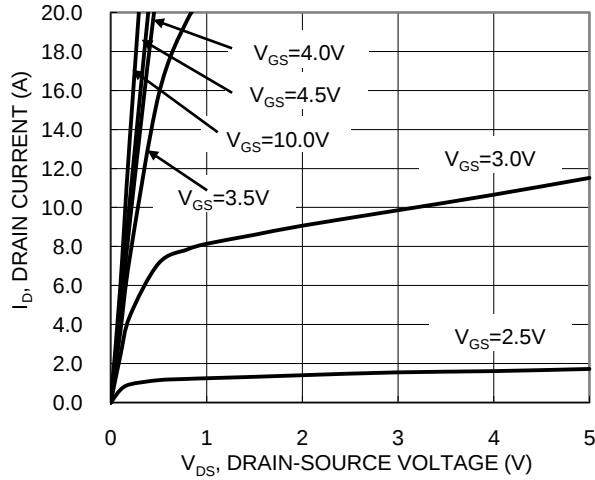


Figure 1. Typical Output Characteristic

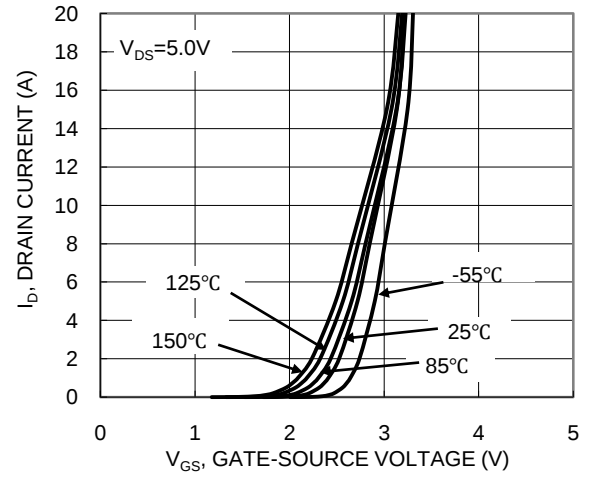


Figure 2. Typical Transfer Characteristic

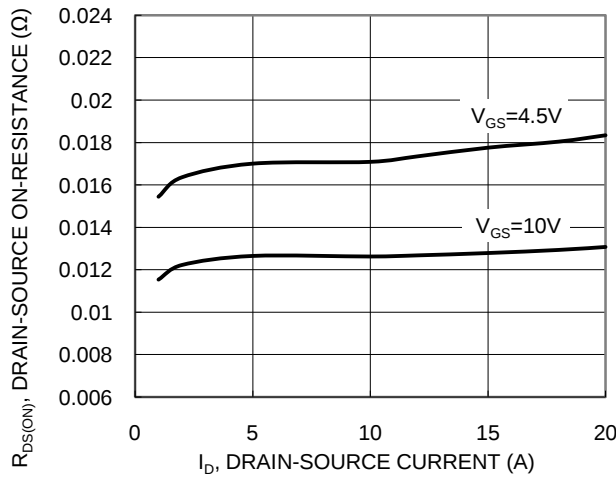


Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

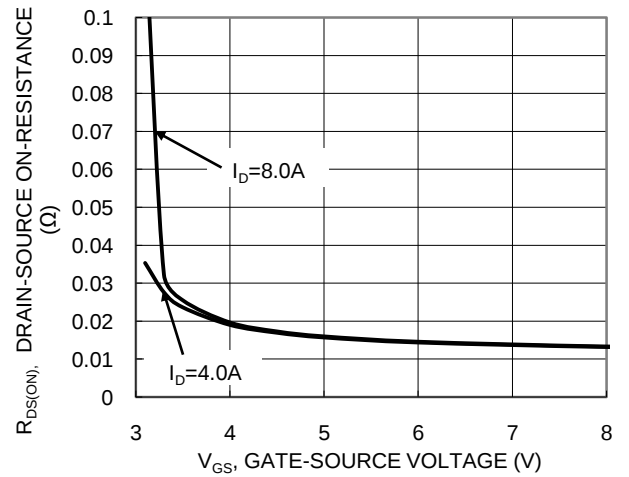


Figure 4. Typical Transfer Characteristic

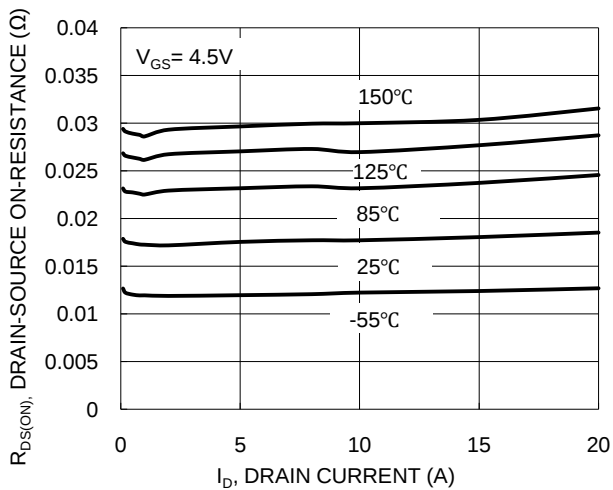


Figure 5. Typical On-Resistance vs. Drain Current and Temperature

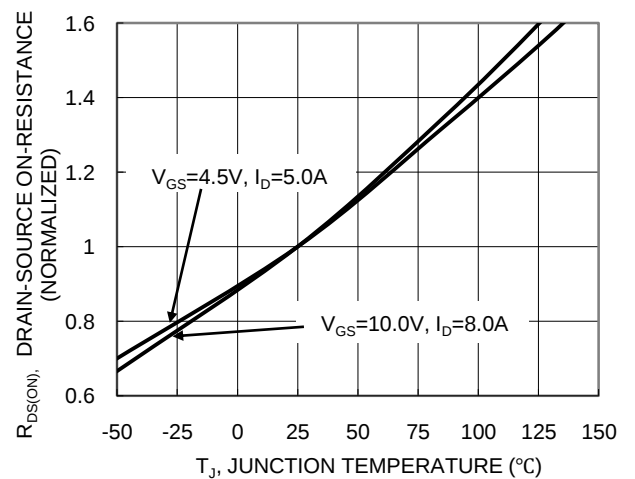


Figure 6. On-Resistance Variation with Temperature

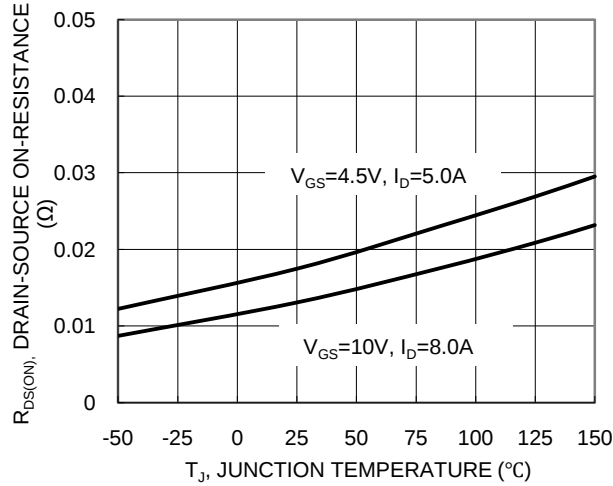


Figure 7. On-Resistance Variation with Temperature

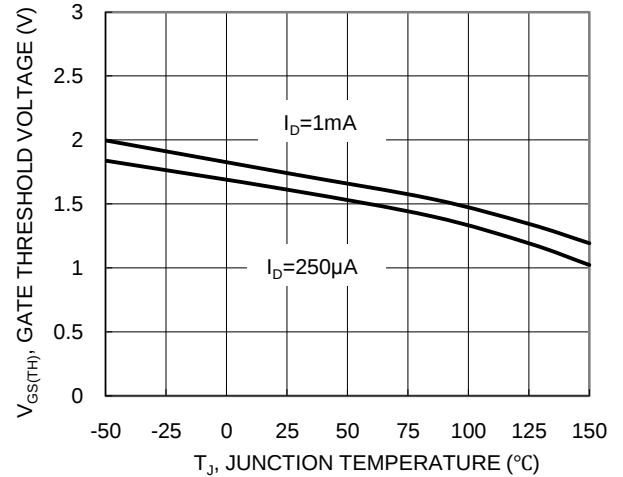


Figure 8. Gate Threshold Variation vs. Junction Temperature

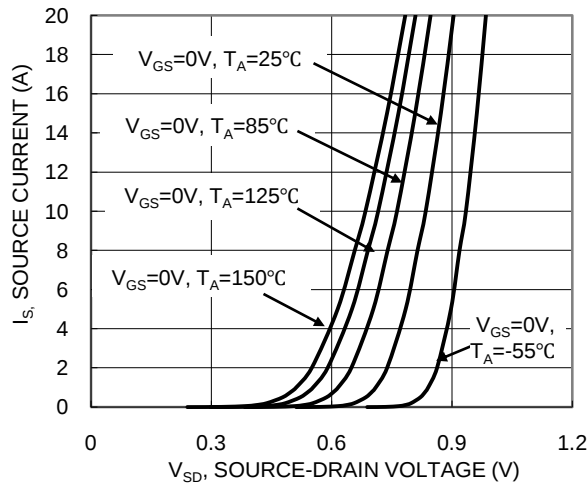


Figure 9. Diode Forward Voltage vs. Current

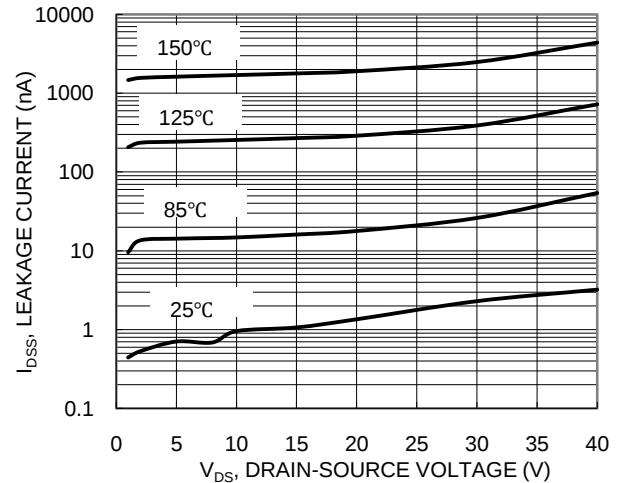


Figure 10. Typical Drain-Source Leakage Current vs. Voltage

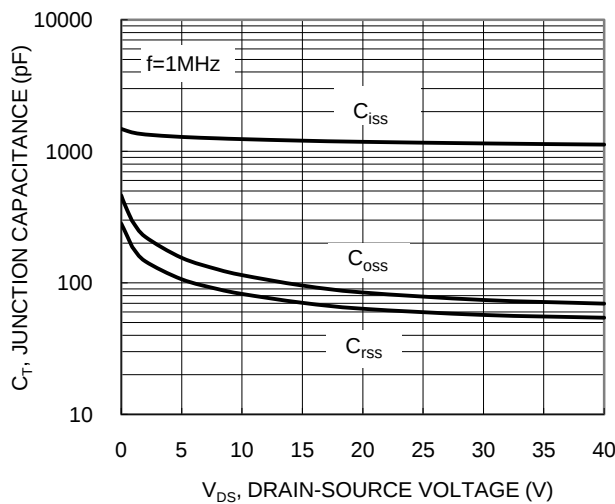


Figure 11. Typical Junction Capacitance

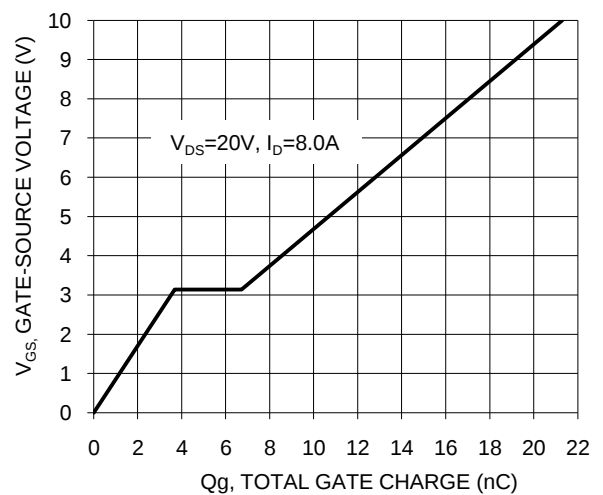


Figure 12. Gate Charge

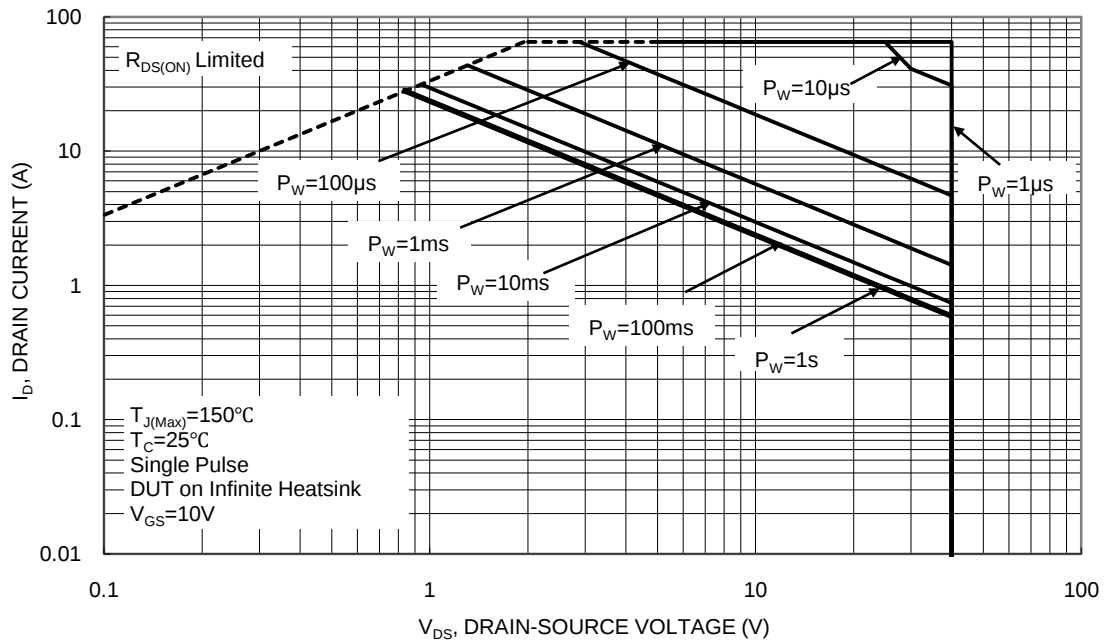


Figure 13. SOA, Safe Operation Area

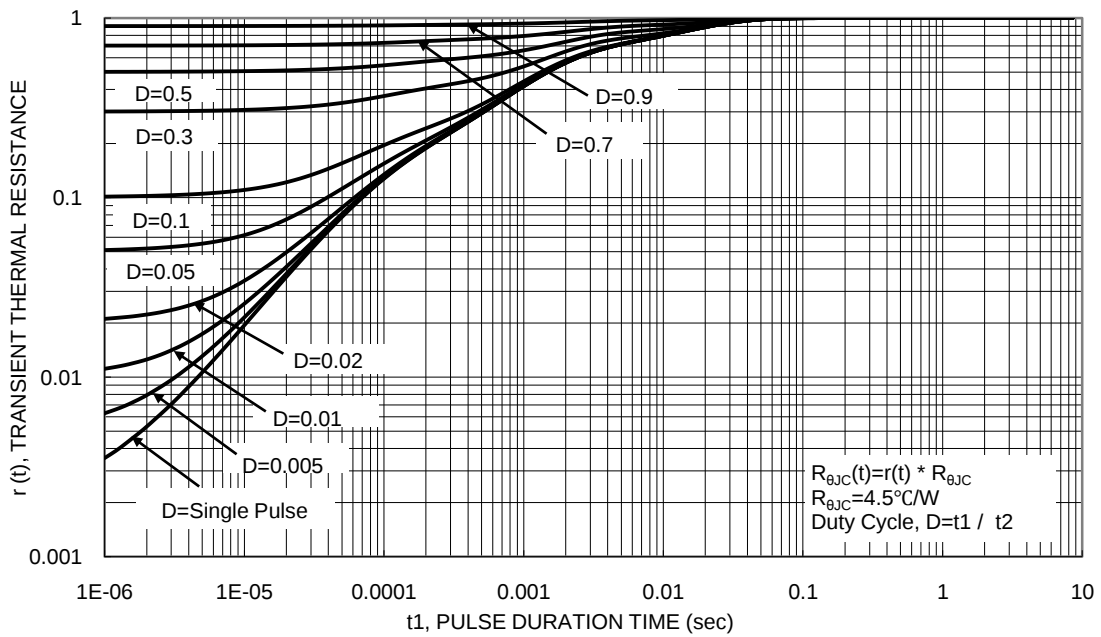
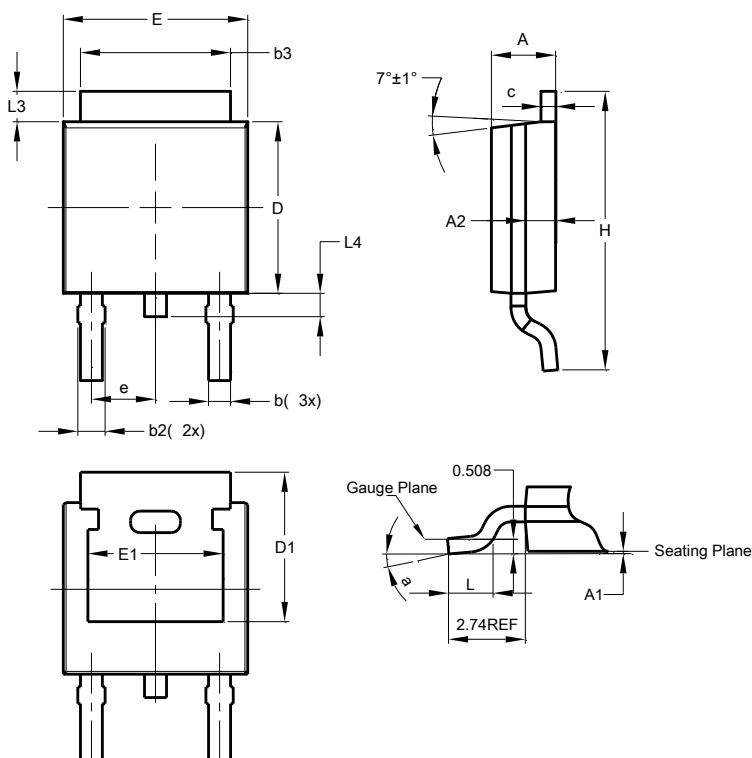


Figure 14. Transient Thermal Resistance

Package Outline Dimensions

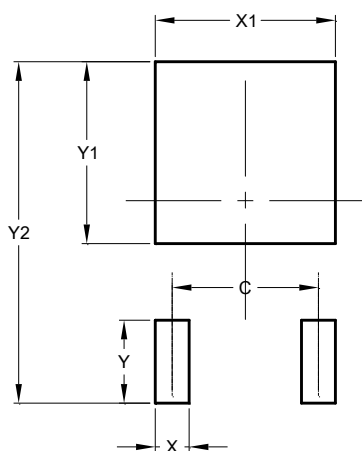
Please see AP02002 at <http://www.diodes.com/datasheets/ap02002.pdf> for the latest version.



TO252 (DPAK)			
Dim	Min	Max	Typ
A	2.19	2.39	2.29
A1	0.00	0.13	0.08
A2	0.97	1.17	1.07
b	0.64	0.88	0.783
b2	0.76	1.14	0.95
b3	5.21	5.46	5.33
c	0.45	0.58	0.531
D	6.00	6.20	6.10
D1	5.21	-	-
e	-	-	2.286
E	6.45	6.70	6.58
E1	4.32	-	-
H	9.40	10.41	9.91
L	1.40	1.78	1.59
L3	0.88	1.27	1.08
L4	0.64	1.02	0.83
a	0°	10°	-
All Dimensions in mm			

Suggested Pad Layout

Please see AP02001 at <http://www.diodes.com/datasheets/ap02001.pdf> for the latest version.



Dimensions	Value (in mm)
C	4.572
X	1.060
X1	5.632
Y	2.600
Y1	5.700
Y2	10.700

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